ABSTRACT OF THE DISCLOSURE

In a solid state image pickup device, in order to form a bypass region with precisely controlled impurity concentration and width, there is provided a solid state image pickup device comprising a photoelectric conversion unit composed of a first region of a first conductive type formed on a semiconductor substrate and having a principal surface, a second region of a second conductive type formed in the first region, and a third region of the first conductive type present between the second region and the principal surface, a fourth region of the second conductive type formed in the first region, and a charge transfer unit including the first region, an insulation layer on the first region and a control electrode provided on the insulation layer, for transferring a signal charge accumulated in the photoelectric conversion unit, to the fourth region, wherein the photoelectric conversion unit and the charge transfer unit are connected through a fifth region of the second conductive type.